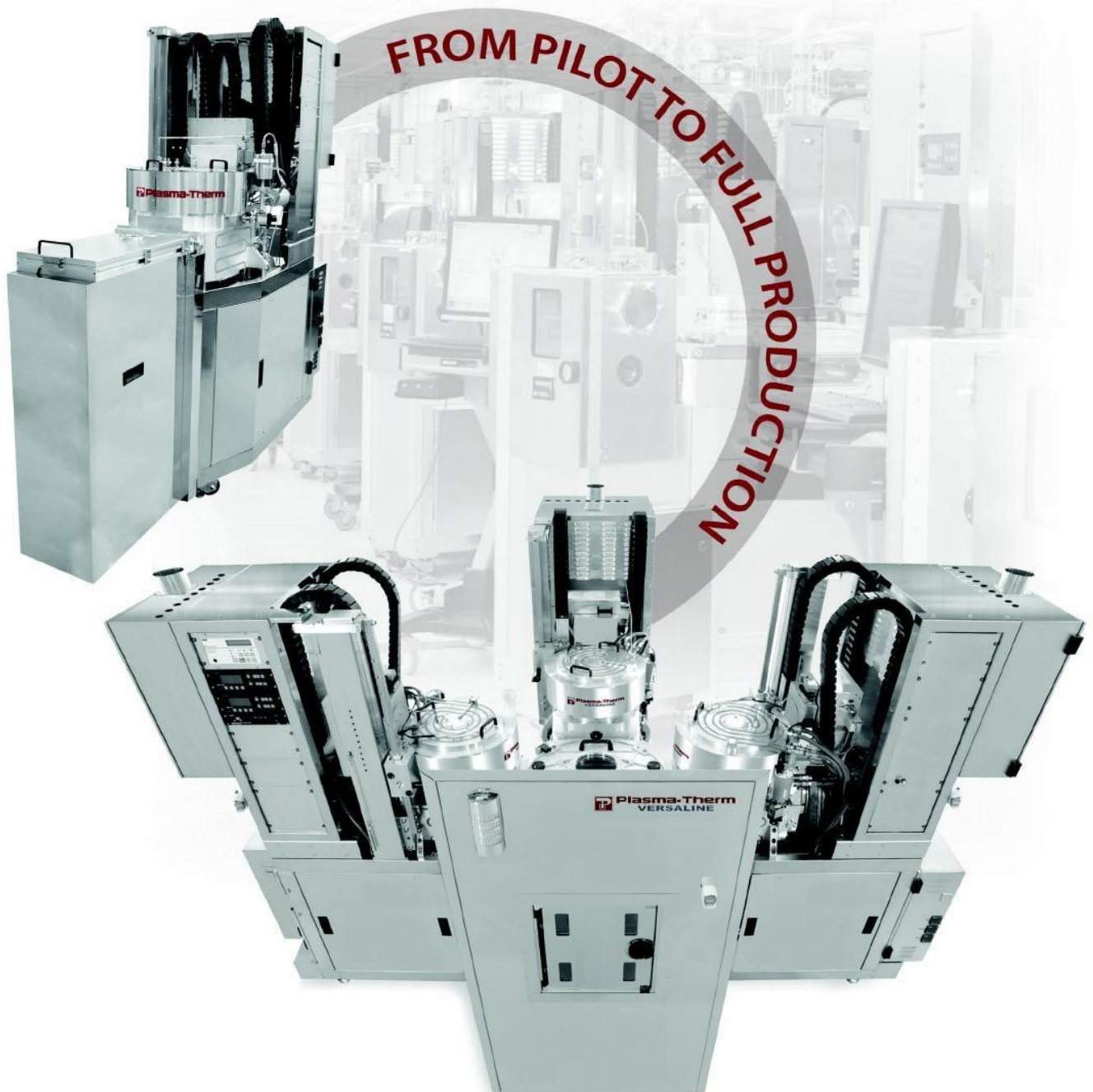




**Deep Silicon Etch™ (DSE) Technology
for Advanced MEMS & TSV Applications**



VERSALINE® DSE

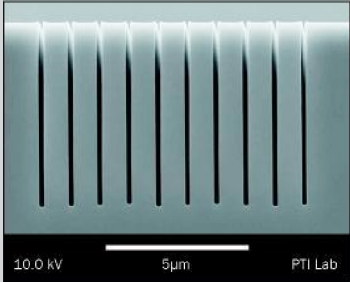
VERSALINE® DSE offers high throughput and low cost of ownership

Complex and high quality MEMS structures are achieved with VERSALINE® DSE IV. Its DRIE technology delivers both Bosch and non-Bosch processing for a wide variety of applications.

VERSALINE DSE incorporates multiple patented innovations, including parameter morphing, fast gas switching, and PID throttle-valve pressure control. These enhanced capabilities allow etching of any shape from big cavities to high-aspect-ratio (up to 60:1) nanostructures. DSE IV provides the highest etch rate, high selectivity to oxide and photoresist, and low damage on sensitive devices such as shiny aluminum. Additional information is available from Plasma-Therm Applications notes.

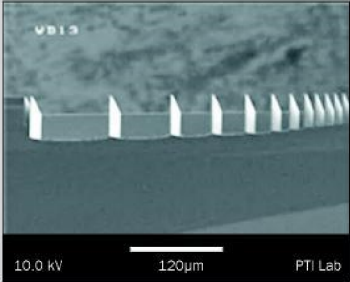
DSE Process Portfolio

Aspect Ratio 60:1




10.0 kV 5µm PTI Lab

A.R.D.E.



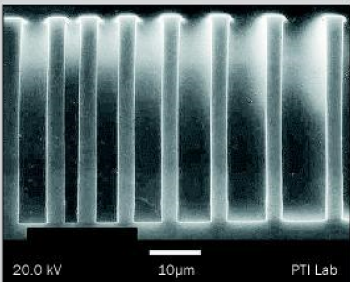
10.0 kV 120µm PTI Lab

**Smooth Sidewalls
roughness <10nm**



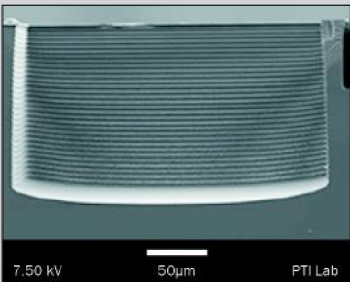
7.50 kV 50µm PTI Lab

Notch Reduction on SOI



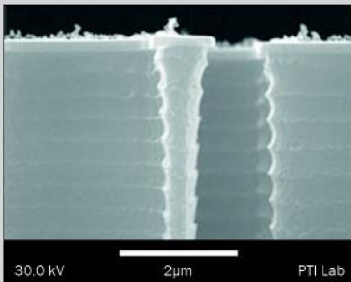
20.0 kV 10µm PTI Lab

High Etch Rate >25µm



7.50 kV 50µm PTI Lab

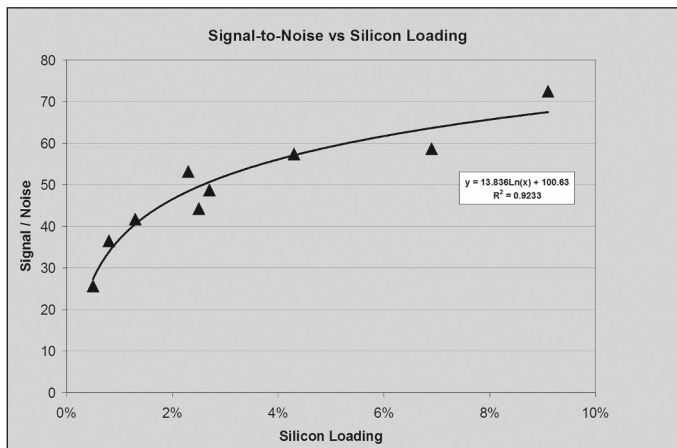
Polymer Removal



30.0 kV 2µm PTI Lab

High Selectivity
Si:PR >200:1 Si:SiO >700:1

End point detection by OES



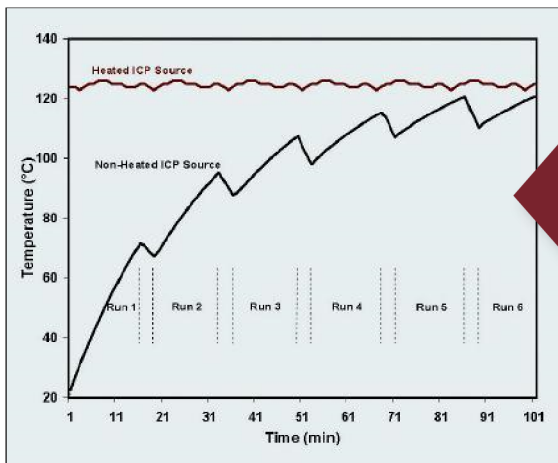
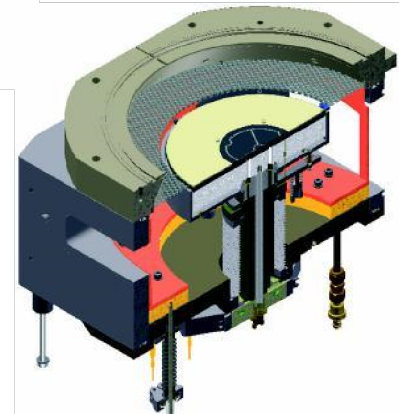
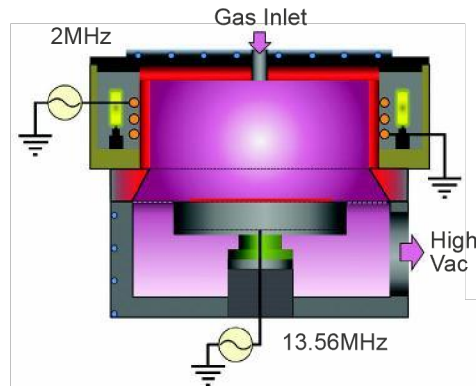
Silicon etching can be stopped on process time, or for greater accuracy, using EndpointWorks detection of the SOI interface. Optical emission spectroscopy (OES) can detect a 1% silicon signal. Laser reflectance or Optical Emission Interferometry (OEI) end point detection systems are also available.

Industrial performance

DSE IV technology was developed for high-volume production and industrial performance, low cost of ownership and high throughput. Low maintenance requirements and high mean time between cleaning are integrated throughout:

- Heated source
- Heated chamber
- Heated throttle valve
- Heated turbo pump and foreline

Process stability and repeatability, both within wafer and wafer-to-wafer meet customers' expectations mainly by having a stable hardware and no by-products deposition on chamber wall.



- Eliminates first-wafer effect
- Improves wafer to wafer repeatability
- Minimizes wet-clean cycle

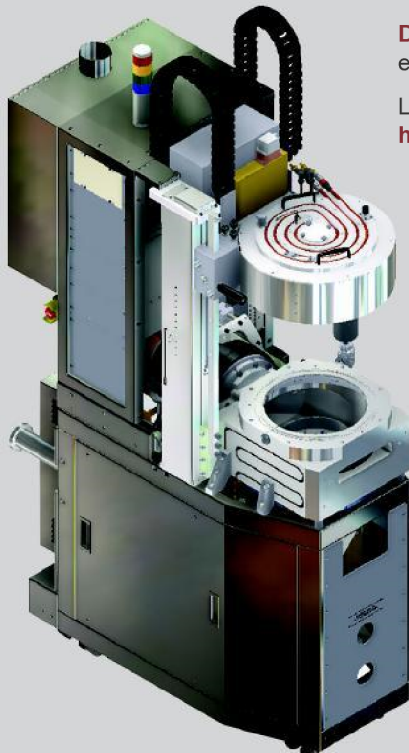
Uptime > 92%
 MTBC > 500 RF hours
 MTTC < 6 hours
 MTBF > 500 RF hours

Easy maintenance

Ergonomic source lift mechanism for **easy chamber cleaning**

Decrease tool offline time with ergonomic maintenance access

Low maintenance time results in **higher productivity**



Rail-mounted turbo pump for **easy maintenance**



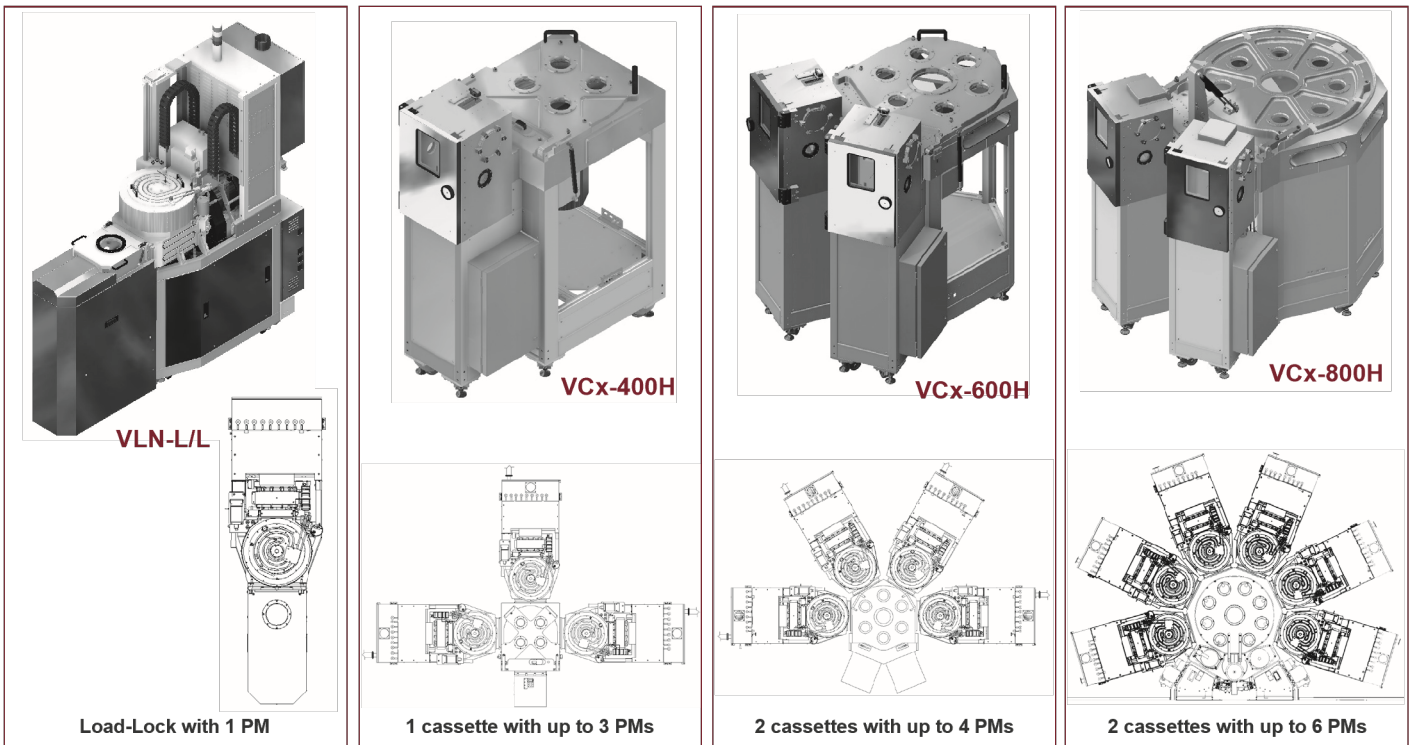
Wafer-size versatility

Process modules and transfer platforms developed by Plasma-Therm are able to clamp and process a wide range of SEMI standard and non-standard wafers:

- 4, 6 and 8 inch diameter wafers
- Si, SiO₂, SOG, glass and other substrates
- Wafer thickness from 120µm to 2mm
- Bow up to 1mm
- Etch-through of all wafers

Integrated optical aligners detect wafer flats or notches if required.

Transfer platform configurations



Universal process modules compatible with multiple transfer platforms

Plasma-Therm has long experience with cluster tools in R&D and production settings, and can recommend the best configuration based on customer need and chemistry. Handling systems and control-software logic minimize cross-contamination.

Support and service

Plasma-Therm provides worldwide technical and service to customers, with hot-line and remote diagnostic support as well as superior on-site service. Spare parts are warehoused in six strategic global locations. Plasma-Therm has been ranked by VLSresearch among the best equipment suppliers for the last 16 years, winning 1st place rankings among etch and clean equipment suppliers for five years in a row.



Plasma-Therm

www.plasmatherm.com

10050 16th St. North • St. Petersburg, FL 33716 • USA

+1 (727) 577-4999